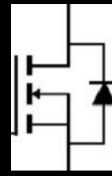


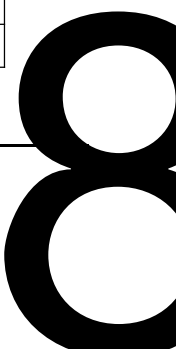
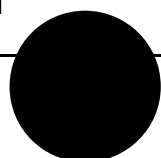
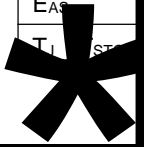


V_{DSS}	V
$R_{DS(on)}$	(typ.)
I_D	96A



Advanced MOSFET process technology | Et |
 Special design

$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	96	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	68	
I_{DM}	Pulsed Drain Current		
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	95	W
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
E_{AS}	Energy per Pulse Average	324	mJ
T_{stg}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

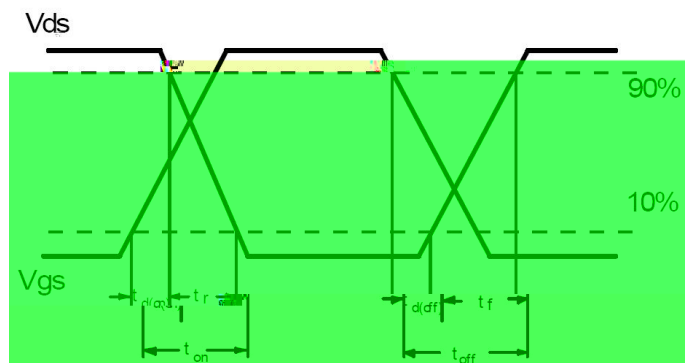
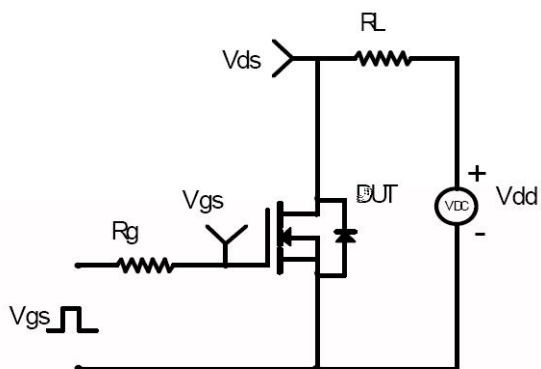
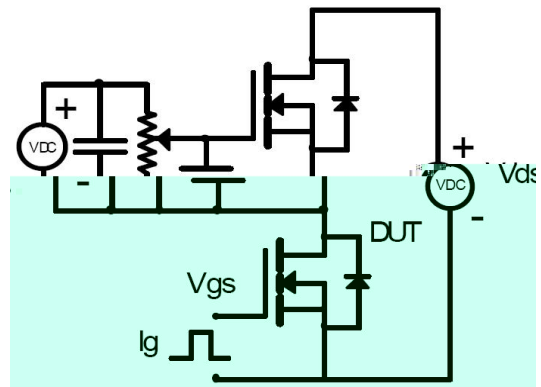
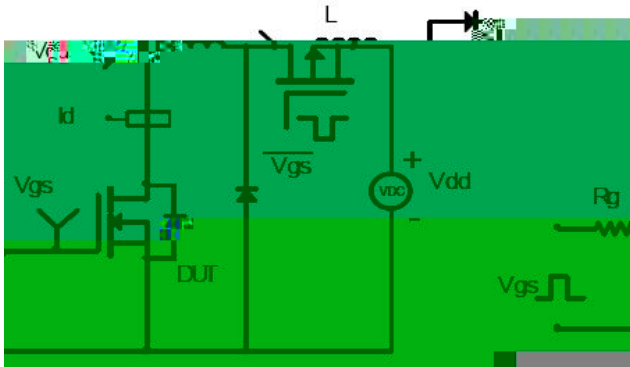




R _{JC}	Junction-to-case	—	1.6	/W

@T_A=25 unless otherwise specified

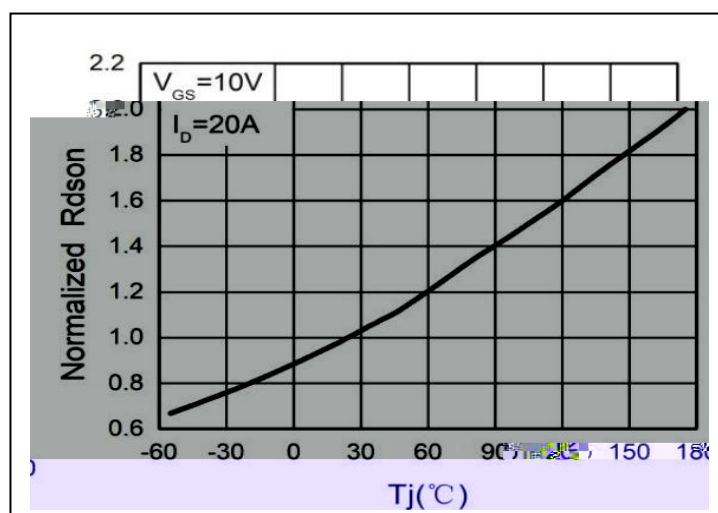
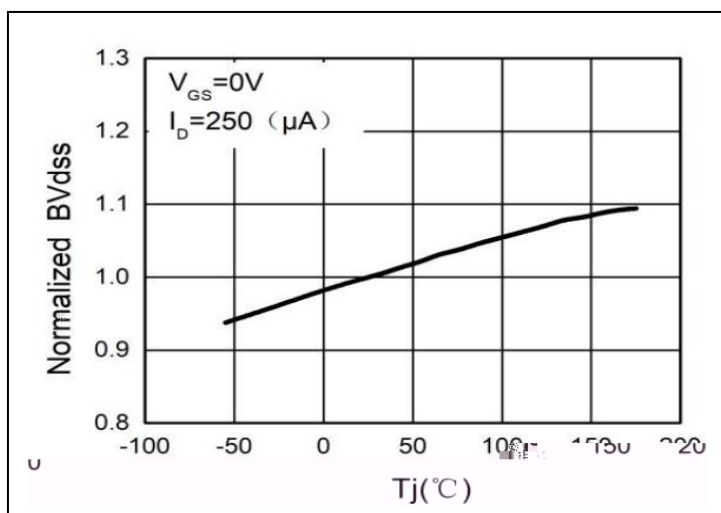
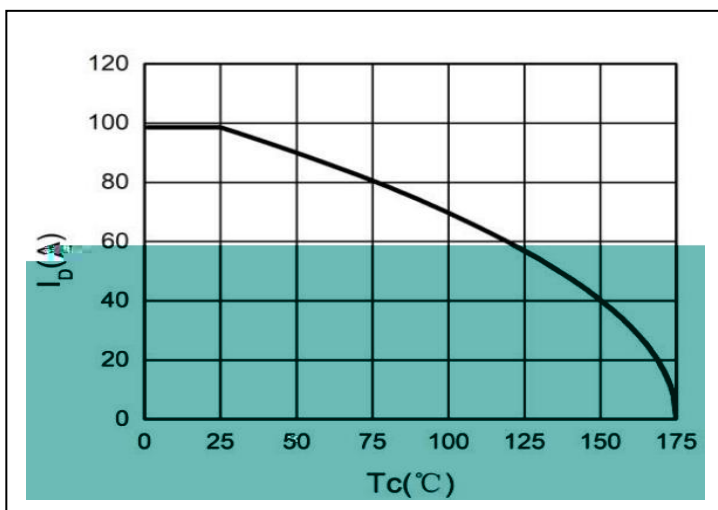
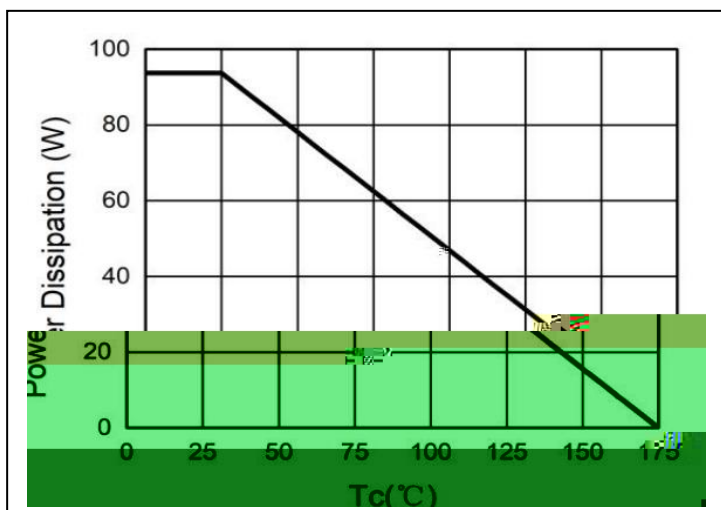
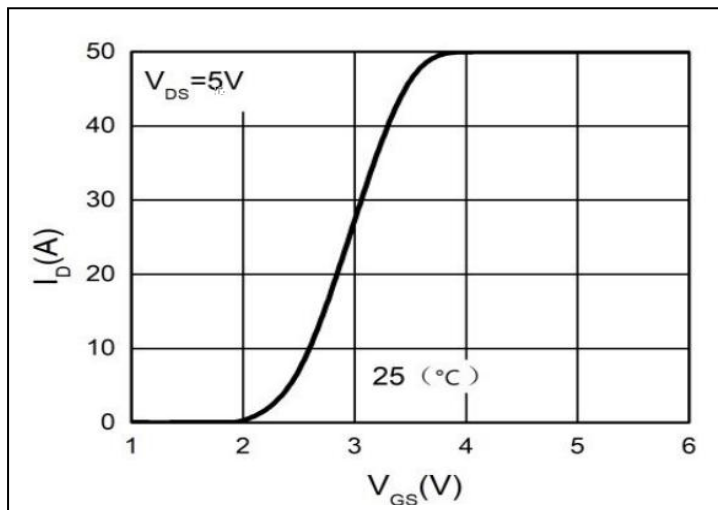
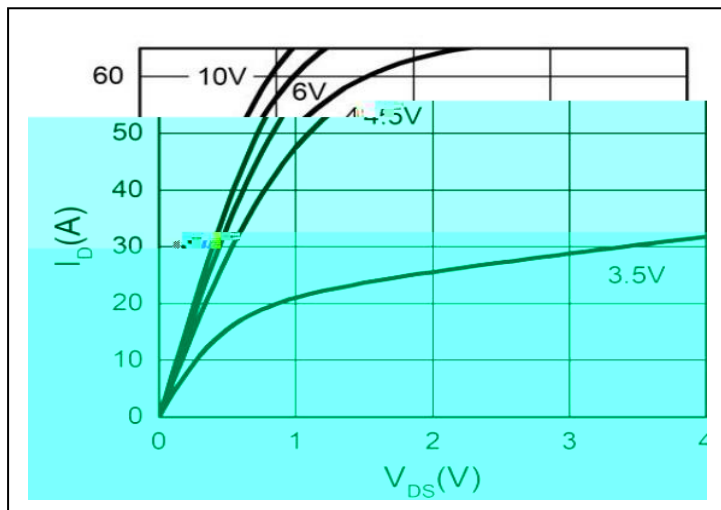
V _{(BR)DSS}	Drain-to-Source breakdown voltage	40	—	—	V	V _{GS} = 0V, I _D = 250μA
R _{DS(on)}	Static Drain-to-Source on-resisfi					

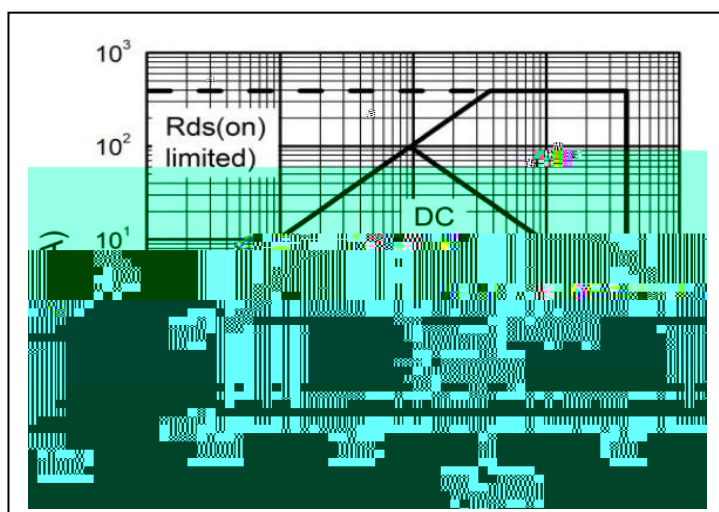
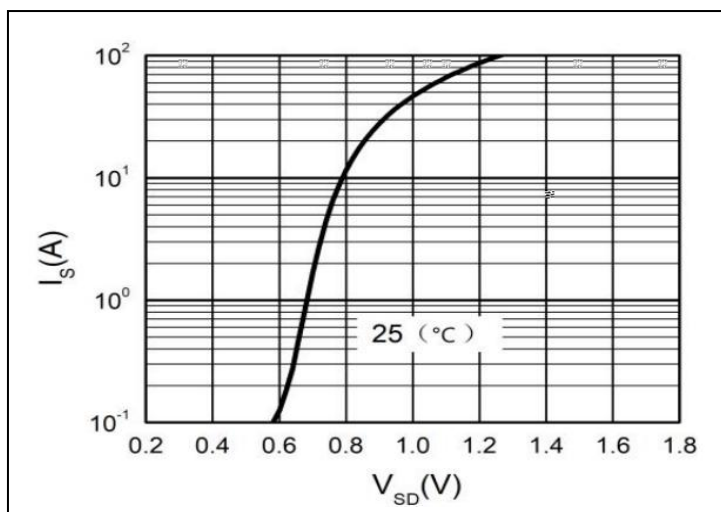
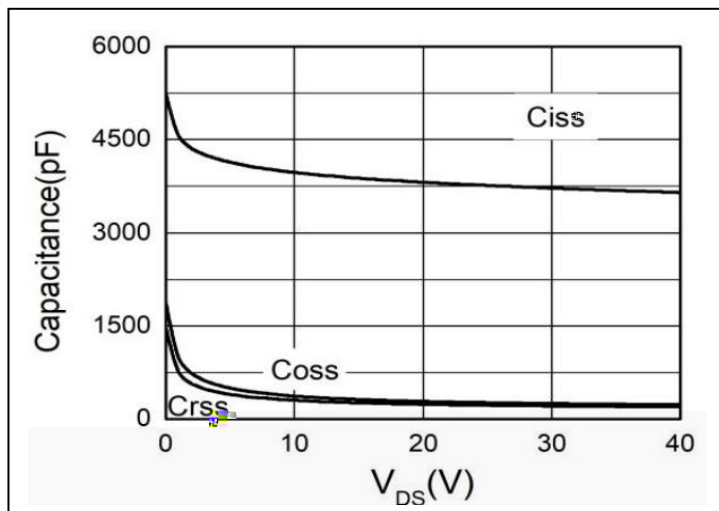
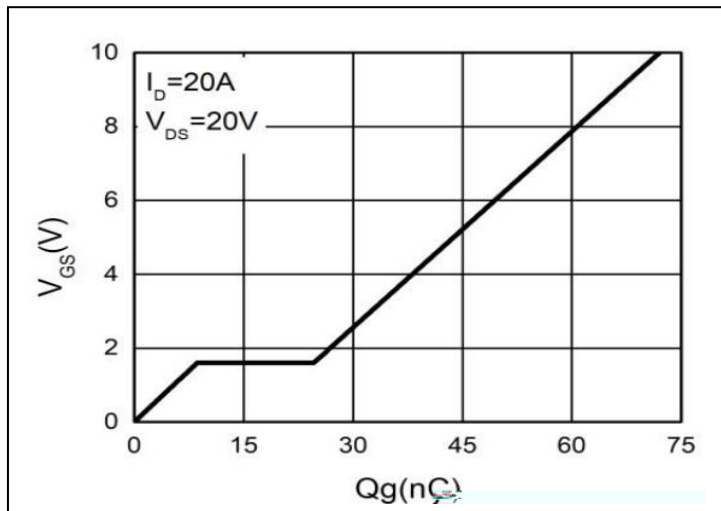


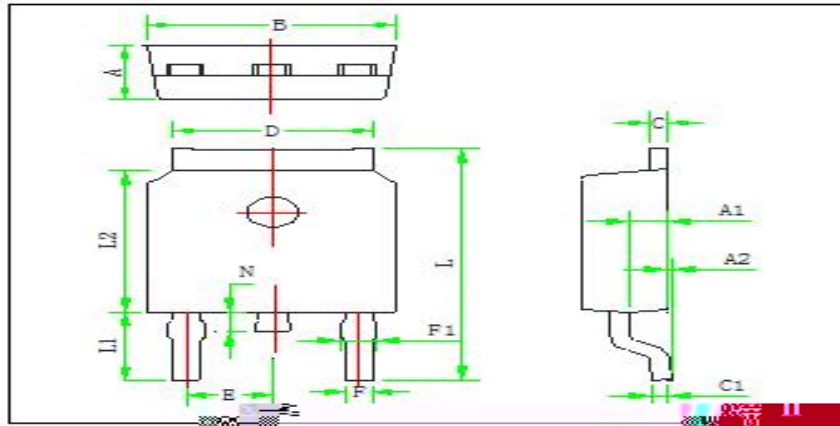
Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.







GENERAL

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Silikron assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (including permissible operating conditions, ranges, or other parameters) listed in products specifications of any and all Silikron products described or contained herein.

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Products Availability and Performance